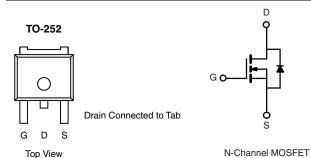


Automotive N-Channel 30 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	30			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.0060			
$R_{DS(on)}$ (Ω) at $V_{GS} = 4.5 \text{ V}$	0.0085			
I _D (A)	50			
Configuration	Single			



FEATURES

- TrenchFET® Power MOSFET
- 100 % R_g and UIS Tested
- AEC-Q101 Qualified
- Material categorization:
 For definitions of compliance please see





ROHS COMPLIANT HALOGEN FREE

ORDERING INFORMATION				
Package	TO-252			
Lead (Pb)-free and Halogen-free	SQD50N03-06P-GE3			

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V_{DS}	30	V	
Gate-Source Voltage		V_{GS}	± 20	V	
Continuous Drain Current ^a	T _C = 25 °C	1	50		
	T _C = 125 °C	- I _D	50		
Continuous Source Current (Diode Conduction) ^a		I _S	50	Α	
Pulsed Drain Current ^b		I _{DM}	200		
Single Pulse Avalanche Current	1 0.1 ml 1	I _{AS}	45		
Single Pulse Avalanche Energy	L = 0.1 mH	E _{AS}	101	mJ	
Maximum Power Dissipation ^b	T _C = 25 °C	D_	83	W	
	T _C = 125 °C		27		
Operating Junction and Storage Temperatur	re Range	T _J , T _{stg}	- 55 to + 175	°C	

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount ^c	R_{thJA}	50	°C/W
Junction-to-Case (Drain)		R_{thJC}	1.8	C/ VV

Notes

- a. Package limited.
- b. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%.$
- c. When mounted on 1" square PCB (FR-4 material).



Automotive N-Channel 30 V (D-S) 175 °C MOSFET

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static				l	•	ı		
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$		30	-	-	V	
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	- V _{GS} , I _D = 250 μA	1.5	2.0	2.5	V	
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	-	± 100	nA	
		V _{GS} = 0 V	V _{DS} = 30 V	-	-	1		
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 30 V, T _J = 125 °C	-	-	50	μΑ	
		V _{GS} = 0 V	V _{DS} = 30 V, T _J = 175 °C	-	-	250	1	
On-State Drain Current ^a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 V$	50	-	-	Α	
		V _{GS} = 10 V	I _D = 20 A	-	0.0047	0.0060		
Drain Cauras On State Besistance	В	V _{GS} = 10 V	I _D = 20 A, T _J = 125 °C	-	-	0.0090	Ω	
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 20 A, T _J = 175 °C	-	-	0.0107		
		V _{GS} = 4.5 V	I _D = 20 A	-	0.0067	0.0085		
Forward Transconductanceb	9 _{fs}	V _{DS} = 15 V, I _D = 20 A		-	74	-	S	
Dynamic ^b								
Input Capacitance	C _{iss}			-	3222	4030		
Output Capacitance	C _{oss}	$V_{GS} = 0 V$	V _{GS} = 0 V V _{DS} = 25 V, f = 1 MHz		563	705	рF	
Reverse Transfer Capacitance	C _{rss}			-	241	300		
Total Gate Charge ^c	Qg			-	25.2	38		
Gate-Source Charge ^c	Q _{gs}	V _{GS} = 4.5 V	$V_{DS} = 15 \text{ V}, I_D = 50 \text{ A}$	-	9.1	-	nC	
Gate-Drain Charge ^c	Q _{gd}			-	9.4	-		
Gate Resistance	R _g	f = 1 MHz		0.5	1.6	2.8	Ω	
Turn-On Delay Time ^c	t _{d(on)}	V_{DD} = 15 V, R_L = 0.3 Ω I_D \cong 50 A, V_{GEN} = 10 V, R_g = 1 Ω		-	10	15		
Rise Time ^c	t _r			-	10	15	- ns	
Turn-Off Delay Time ^c	t _{d(off)}			-	26	39		
Fall Time ^c	t _f			-	9	14		
Source-Drain Diode Ratings and Chara	acteristics ^b				•			
Pulsed Current ^a	I _{SM}			-	-	200	Α	
Forward Voltage	V _{SD}	I _F = 85 A, V _{GS} = 0 V		-	1	1.5	V	

Notes

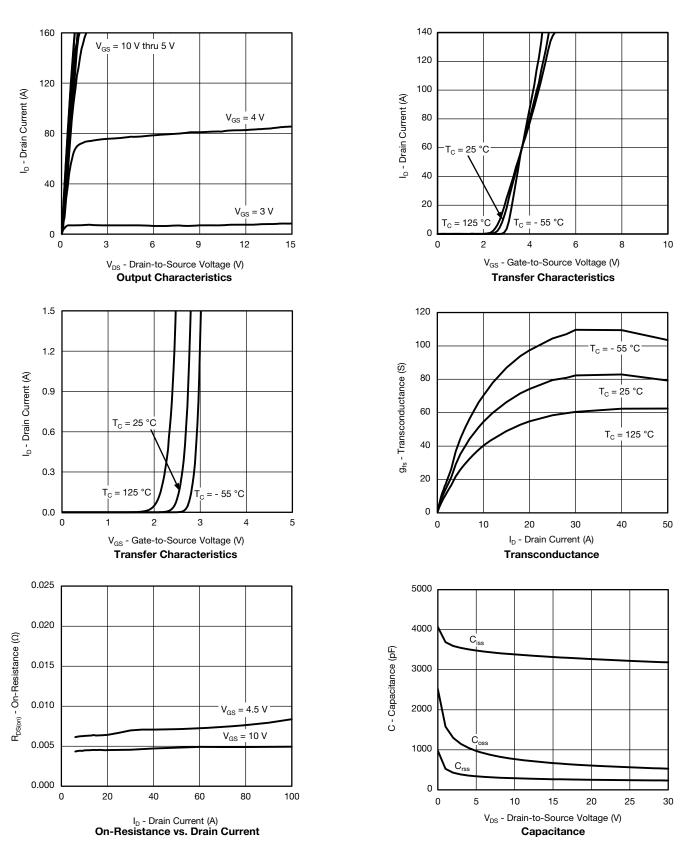
- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



Automotive N-Channel 30 V (D-S) 175 °C MOSFET

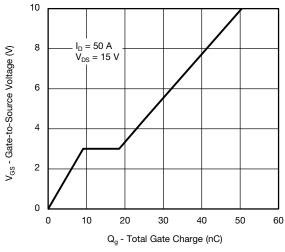
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



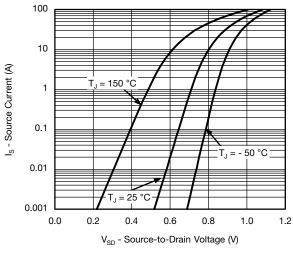


Automotive N-Channel 30 V (D-S) 175 °C MOSFET

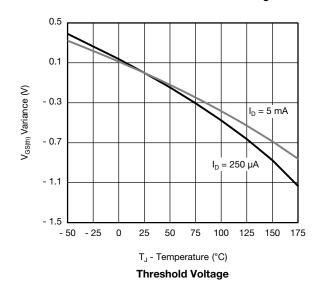
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

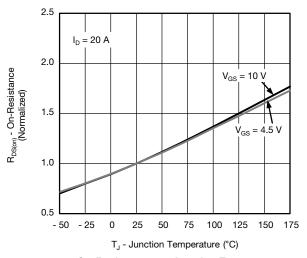


Gate Charge

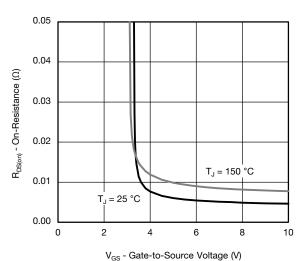


Source Drain Diode Forward Voltage

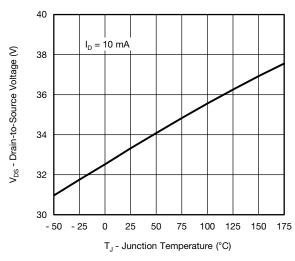




On-Resistance vs. Junction Temperature



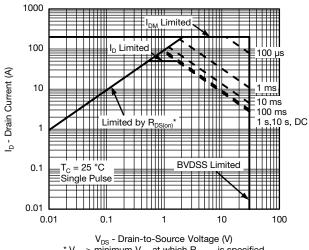
On-Resistance vs. Gate-to-Source Voltage



Drain Source Breakdown vs. Junction Temperature

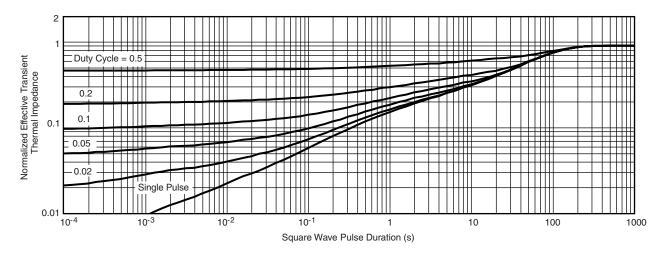
Automotive N-Channel 30 V (D-S) 175 °C MOSFET

THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



* V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

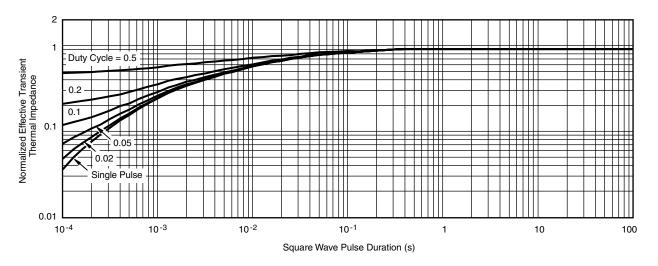
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient

Automotive N-Channel 30 V (D-S) 175 °C MOSFET

THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

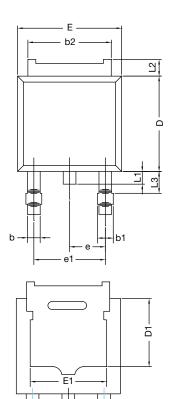
Note

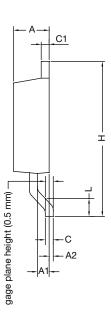
- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.



Automotive N-Channel 30 V (D-S) 175 °C MOSFET

TO-252AA CASE OUTLINE





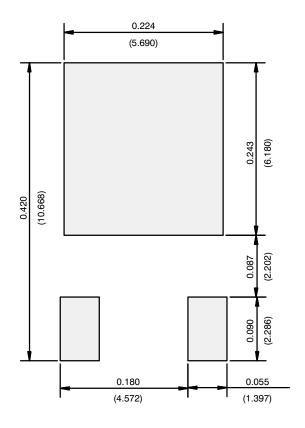
	MILLIMETERS		INCHES		
DIM.	MIN.	MAX.	MIN.	MAX.	
Α	2.21	2.38	0.087	0.094	
A1	0.89	1.14	0.035	0.045	
A2	0.030	0.127	0.001	0.005	
b	0.71	0.88	0.028	0.035	
b1	0.76	1.14	0.030	0.045	
b2	5.23	5.44	0.206	0.214	
С	0.46	0.58	0.018	0.023	
C1	0.46	0.58	0.018	0.023	
D	5.97	6.22	0.235	0.245	
D1	4.10	4.45	0.161	0.175	
Е	6.48	6.73	0.255	0.265	
E1	4.49	5.50	0.177	0.217	
е	2.28 BSC		0.090 BSC		
e1	4.57 BSC		0.180 BSC		
Η	9.65	10.41	0.380	0.410	
L	1.40	1.78	0.055	0.070	
L1	0.64	1.02	0.025	0.040	
L2	0.89	1.27	0.035	0.050	
L3	1.15	1.52	0.040	0.060	
ECN: T11-0110-Rev. L, 18-Apr-11 DWG: 5347					

Note

• Dimension L3 is for reference only.

Automotive N-Channel 30 V (D-S) 175 °C MOSFET

RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads Dimensions in Inches/(mm)

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Automotive N-Channel 30 V (D-S) 175 °C MOSFET

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